REMARKS

The present Preliminary Amendment is submitted to delete the multiple dependency of the claims, thereby placing such claims in condition for examination and reducing the required PTO filing fee.

Attached hereto is a marked-up version of the changes made to the claims by the current Preliminary Amendment. The attached page is captioned "**Version With Markings to Show Changes Made**".

Respectfully submitted,

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THE COMMISSIONER IS AUTHORIZED TO CHARGE ANY DEFICIENCY IN THE FEES FOR THIS PAPER TO DEPOSIT ACCOUNT NO. 23-0975

CLAIMS

1. A method for inspecting a semiconductor wafer surface, comprising the steps of scanning a wafer with a laser beam, detecting a scattered or reflected light from the wafer surface by multiple light optics having different detecting angles to an incident light, and classifying the defect into some characteristics based on the ratio of the detected light intensities from the multiple light optics.

2. A method for inspecting a semiconductor wafer surface, comprising the steps of scanning a wafer with a laser beam, detecting a scattered or reflected light from the wafer surface by multiple light optics having different detecting angles to an incident light, calculating a difference between a horizontal length and a vertical height or between a horizontal length and a horizontal length crossing at right angles of a LPD (Light Point Defect) present on the wafer surface from a difference in the standard particle conversion sizes based on the ratio of the detected light intensities from the multiple light optics, and determining the forms and types of defects and the like present on the wafer surface.

3. A method for inspecting a semiconductor wafer surface according to Claim 1 [or] 2, wherein a laser surface inspection apparatus having at least two light optics to one incidence is used as a laser surface inspection apparatus. Claim 1.

4. A method for inspecting a semiconductor wafer surface according to [any] of Claims 1-3, wherein the semiconductor wafer is an epitaxial semiconductor wafer. Claim 1.

5. A method for inspecting a semiconductor wafer surface according to [any] of Claims 1-4, wherein the forms and types of defects and the like are determined depending on a combination of A, B, and a value given by A/B, where the detected light intensity or standard particle conversion size of a LPD (Light Point Defect) detected in a high-angle light optic is A, while the detected light intensity or standard particle conversion size of the LPD detected in a low-angle light optic is B. Claim 1.

6. A method for inspecting a semiconductor wafer surface according to [any] of Claims 1-4, wherein the forms and types of defects and the like are determined based on Table 1, where the standard particle conversion size of a LPD (Light Point Defect) detected in a high-angle light optic is A, while the standard particle conversion size of the LPD detected in a low-angle light optic is B.

Table 1

Relations between A and B or ranges	Actual for ms
A≧B×1．13	Stacking Fault
A<B×1．13	Non-epi-layer originated extraneous substance (adherent particle)
B<90nm and A>107nm	Micro-crystallographic-defect (hillock, shadow, dislocation)
B>160nm and A<107nm	Abnormal growth (large-pit, projection)
Others	Abnormal product

Claim 1

7. A method for inspecting a semiconductor wafer surface according to any of Claims 1-3, wherein the semiconductor wafer is a mirror-finished semiconductor wafer.

8. A method for inspecting a semiconductor wafer surface according to Claim 7, wherein the forms and types of defects and the like are determined depending on a combination of A, B, and a value given by A/B, where the detected light intensity or standard particle conversion size of a LPD (Light Point Defect) detected in a high-angle light optic is A, while the detected light intensity or standard particle conversion size of the LPD detected in a low-angle light optic is B.

Claim 1

9. A method for inspecting a semiconductor wafer surface according to any of Claims 1-3 and 7, wherein the forms and types of defects and the like are determined based on Table 2, where the standard particle conversion size of a LPD (Light Point Defect) detected in a high-angle light optic is A, while the standard particle conversion size of the LPD detected in a low-angle light optic is B.

Table 2

Relations between A and B or ranges	Actual for ms
A≧B×1．13 or B<90nm and A>107nm	Scratch, flaw, and shallow pit
A<B×1．13	Adherent particle or COP
B≧85nm and A<107nm	Grown-in defect in bulk near surface